

## **NCE N-Channel Super Trench Power MOSFET**

### **Description**

The NCEP6090AK uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

V<sub>DS</sub> =60V,I<sub>D</sub> =90A

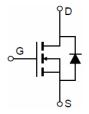
 $R_{DS(ON)} < 8.0 \text{m}\Omega$  @  $V_{GS} = 10V$  (Typ:7.2m $\Omega$ )  $R_{DS(ON)} < 9.5 \text{m}\Omega$  @  $V_{GS} = 4.5V$  (Typ:8.6m $\Omega$ )

- Excellent gate charge x R<sub>DS(on)</sub> product
- Very low on-resistance R<sub>DS(on)</sub>
- Pb-free lead plating
- 100% UIS tested

### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED! 100% ΔVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-252 -2Ltop view

### **Package Marking and Ordering Information**

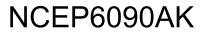
Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP6090AK	NCEP6090AK	TO-252-2L	-	-	-

Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	90	А
Drain Current-Continuous(T <sub>C</sub> =100℃)	I <sub>D</sub> (100℃)	63.6	Α
Pulsed Drain Current	I <sub>DM</sub>	360	А
Maximum Power Dissipation	P <sub>D</sub>	85	W
Derating factor		0.68	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	320	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	1.76	°C/W
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# Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	On Characteristics (Note 3)					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.2	1.7	2.5	V
Drain-Source On-State Resistance	-	V <sub>GS</sub> =10V, I <sub>D</sub> =45A	-	7.2	8.0	mΩ
Dialii-Source Oil-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =45A	-	8.6	9.5	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =45A	-	35	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V -20V/V -0V	-	2100	-	PF
Output Capacitance	Coss	$V_{DS}$ =30V, $V_{GS}$ =0V, F=1.0MHz	-	359	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	Γ=1.UIVIΠ2	-	12	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $I_{D}$ =45 $A$	-	2	-	nS
Turn-Off Delay Time	$t_{d(off)}$	$V_{GS}$ =10 $V$ , $R_{G}$ =4.7 $\Omega$	-	29	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg	\/ -20\/ L -4FA	-	36.6		nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=30V,I_{D}=45A,$	-	6.7		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	5.8		nC
Drain-Source Diode Characteristics			•			•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =45A	-		1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	90	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = I_S$	-	38		nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	48		nC

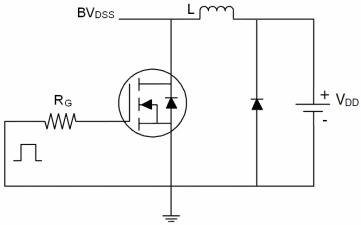
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=30V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

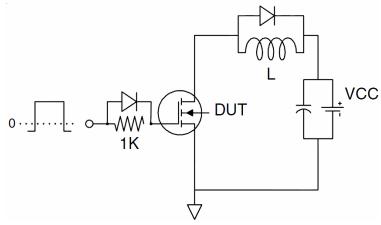


## **Test Circuit**

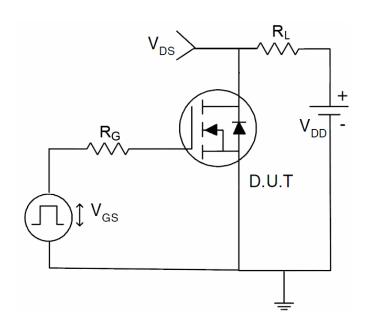
# 1) E<sub>AS</sub> test Circuit



## 2) Gate charge test Circuit

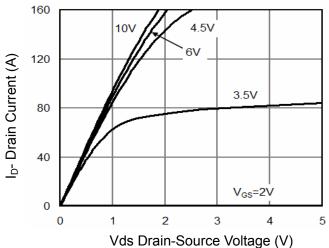


## 3) Switch Time Test Circuit

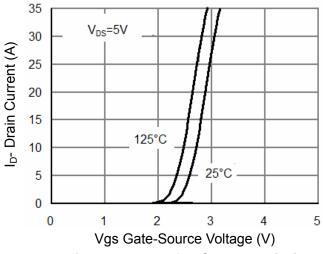




## **Typical Electrical and Thermal Characteristics**



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

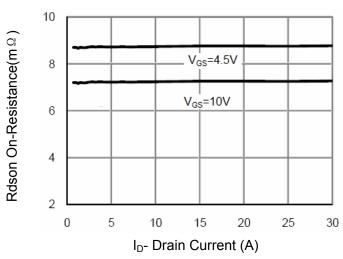


Figure 3 Rdson- Drain Current

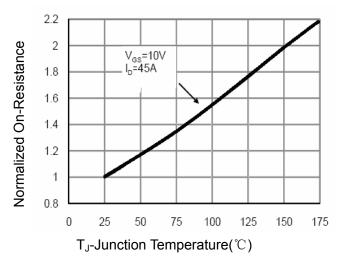


Figure 4 Rdson-JunctionTemperature

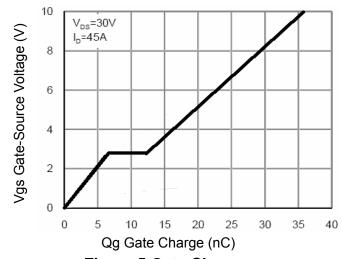


Figure 5 Gate Charge

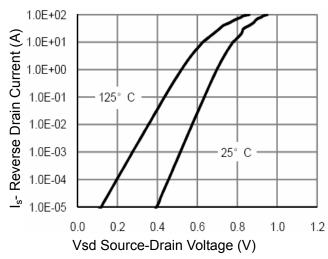


Figure 6 Source- Drain Diode Forward



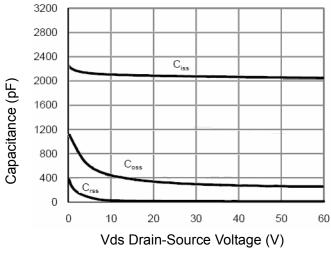


Figure 7 Capacitance vs Vds

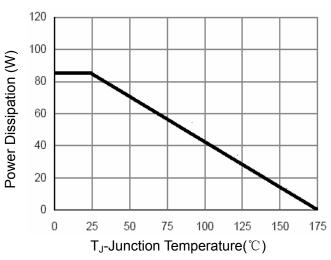
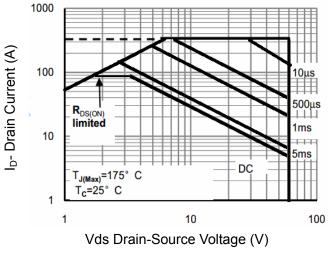


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

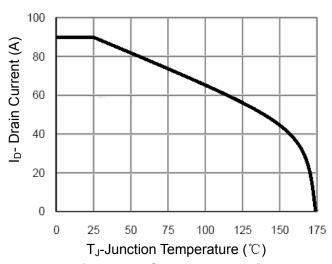
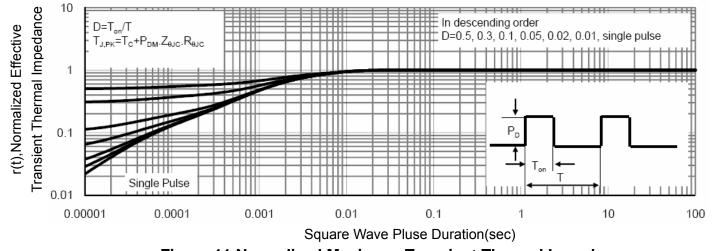


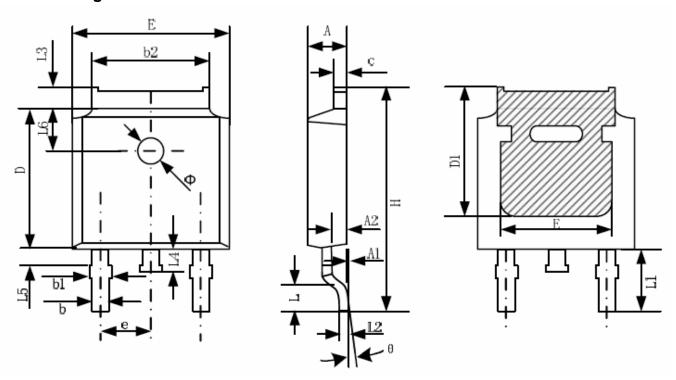
Figure 10 Current De-rating



**Figure 11 Normalized Maximum Transient Thermal Impedance** 



# **TO-252-2L Package Information**



Comple at	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α	2.20	2.38 0.087		0.094	
A1	0.00	0.10	0.000	0.004	
A2	0.90	1.10	0.035	0.043	
b	0.72	0.85	0.028	0.033	
b1	0.72	0.90	0.028	0.035	
b2	5.13	5.46	0.202	0.215	
С	0.47	0.60	0.019	0.024	
D	6.00	6.20	0.236	0.244	
D1	5.25		0.207		
Е	6.50	6.70	0.256	0.264	
E1	4.70		0.185		
e	2.19	2.39	0.086	0.094	
Н	9.80	10.40	0.386	0.409	
L	1.40	1.70	0.055	0.067	
L1	2.90	REF	0.114 REF		
L2	0.508	BSC	0.020 BSC		
L3	0.90	1.25	0.035	0.049	
L4	0.60	1.00	0.024	0.039	
L5	0.15	0.75	0.006	0.030	
L6	1.80 REF		0.071 REF		
Φ	1.20	1.40	0.047	0.055	
θ	0°	8°	0°	8°	

#### http://www.ncepower.com

# NCEP6090AK

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